

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1-6. (Cancelled).

7. (Currently amended) A polishing method which is part of a method for fabricating a semiconductor device, the fabrication method including the process step of polishing a substrate using CMP,

wherein in the polishing process step, a tube-type slurry supply pump is used for supplying a slurry, and

wherein in the tube-type slurry supply pump, a tube which substantially does not contain fine particles for reinforcing the strength of the tube is used as a tube for supplying the slurry,
and

wherein the tube is a vinyl chloride type tube.

8. (Cancelled)

9. (Currently amended) A method for fabricating a semiconductor device, comprising the polishing method of claim 7 any one of claims 1 through 8.

10. (Currently amended) A system for polishing a substrate using CMP, comprising:

a CMP apparatus for polishing the substrate; and

a tube-type slurry supply pump for supplying a slurry during polishing,

wherein a tube for the tube-type slurry supply pump is a tube in which at least the inner surface is formed of a vinyl chloride material, and

wherein the tube is a vinyl chloride type tube.

11-16. (Cancelled)

17. (Currently amended) ~~The polishing method of claim 15 A device formation method comprising the steps of:~~

placing a substrate in a CMP unit,

supplying a slurry on the substrate through a tube connected to a slurry pump, and

polishing the substrate on which the slurry is supplied,

wherein the tube has at least an inner surface formed of a vinyl chloride material.

18. (Currently amended) A device formation method comprising of,

placing a substrate in a CMP unit,

supplying a slurry on the substrate through a tube connected to a slurry pump, and

polishing the substrate on which the slurry is supplied, and

wherein the tube is a vinyl chloride type tube.

19. (Currently amended) A system for forming a semiconductor device comprising:

a CMP unit for polishing a substrate;

a slurry pump for supplying a slurry to the CMP unit; and

a tube connected between the CMP unit and the slurry pump, and

wherein the tube is a vinyl chloride type tube substantially does not contain fine particles

for reinforcing the strength of the tube.

20. (Cancelled)

21. (Currently amended) A system for forming a semiconductor device comprising:
- a CMP unit for polishing a substrate;
 - a slurry pump for supplying a slurry to the CMP unit; and
 - a tube connected between the CMP unit and the slurry pump, and
- wherein the tube has at least an inner surface formed of a vinyl chloride material.